

Faster G_0W_0 implementation for more accurate material design

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Abstract

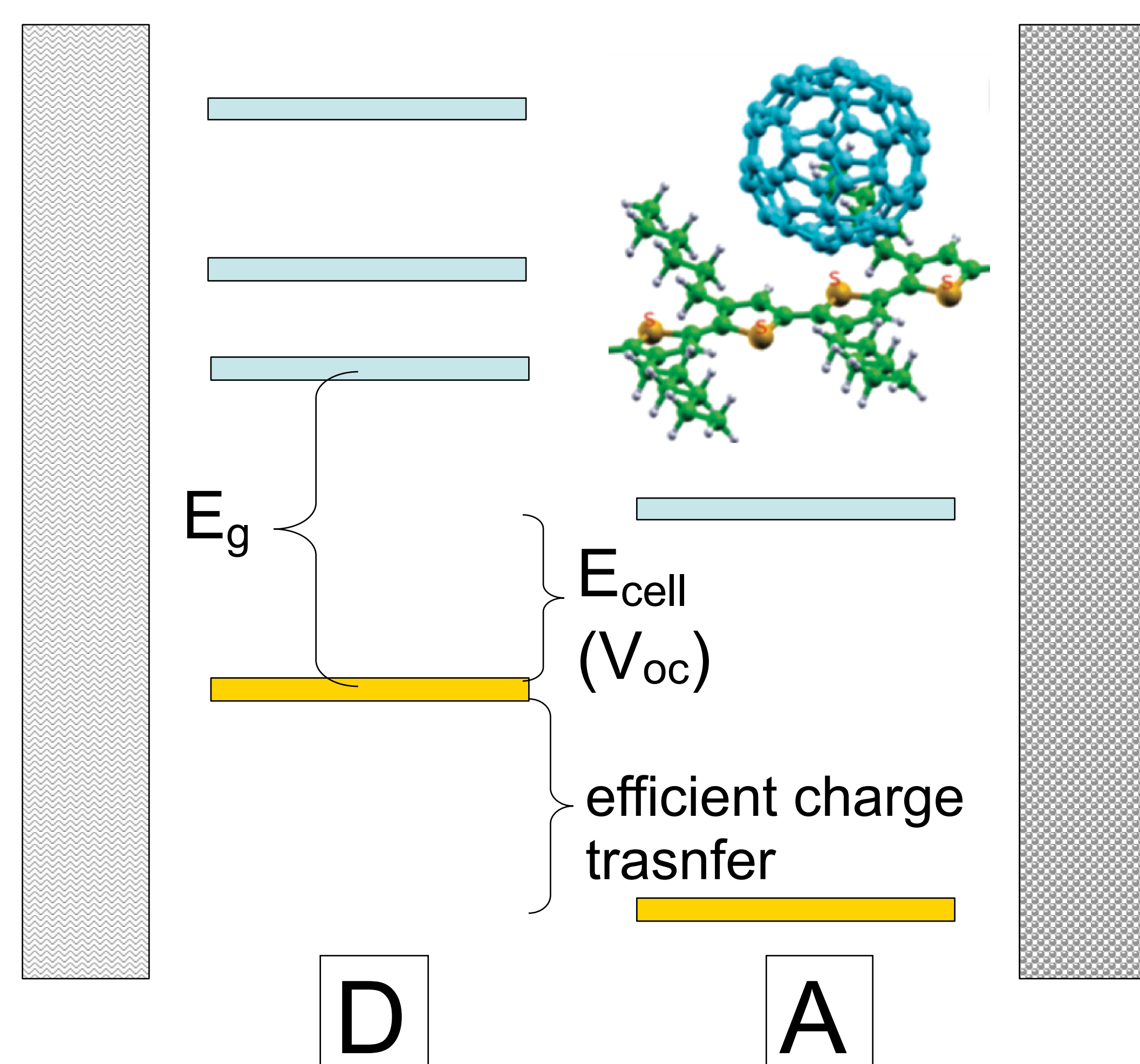
Density-functional theory (DFT) is currently the *ab initio* method most widely used to predict electronic energy levels of new molecules. However, approximations intrinsic to the theory limit the accuracy of calculated energy levels to about ± 0.5 eV. More efficient theoretical design of molecules and materials could be achieved if more precise methods were available. The G_0W_0 approach is an *ab initio* method that provides such an enhanced precision, with predicted energy levels accurate to about ± 0.05 eV. However, such calculations are currently prohibitive for systems with more than a few tens of electrons, thus limiting their use in many applications. What limits calculations to this system size in traditional plane waves (PW) implementations of G_0W_0 is the need to invert the dielectric matrix in a large PW basis and the need to carry out summations over a large number of conduction states. This poster presents a strategy to avoid both of these bottlenecks.

Material design : organic photovoltaics

Criteria :

- Gap : optimal for solar spectrum
- Ionisation Energy (IE) :
 - lower than C_{60} (for good charge transfer)
 - high enough for good V_{oc} and air stability

Morale: Precise electron removal and addition energies are crucial in some applications



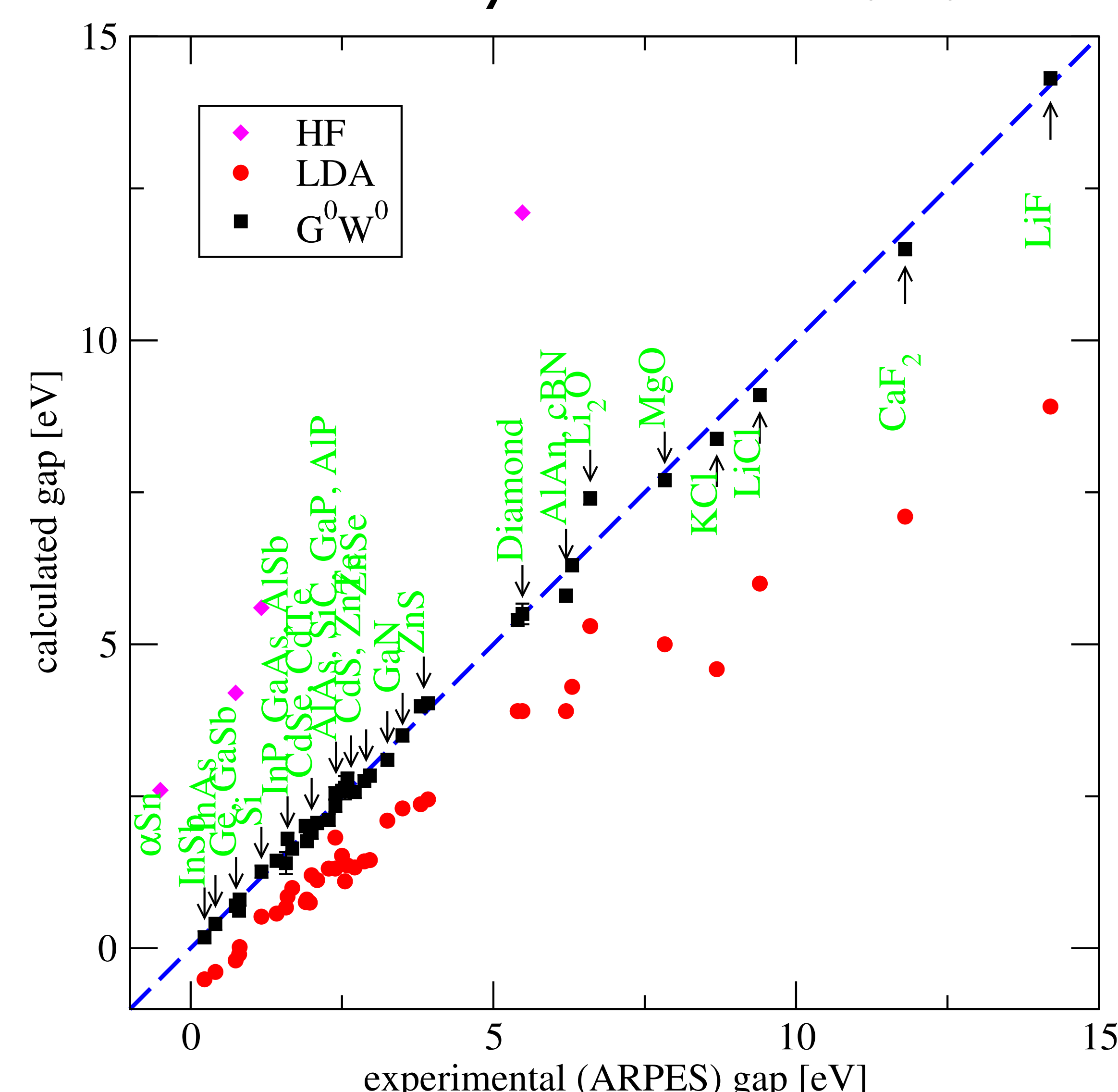
The G_0W_0 method

DFT levels offer quick sorting of candidate materials.

Further refinement is still desirable given the resources and time required to synthesize a new material.

G_0W_0 can provide such results

Accuracy of DFT and G_0W_0



In G_0W_0 , DFT eigenstates and eigenvalues are used as a starting point :

$$(\hat{T} + \hat{V}_{ext} + \hat{V}_{xc})|n\rangle = \varepsilon_n|n\rangle$$

They are then corrected to first order in perturbation theory using the GW exchange-correlation operator $\hat{\Sigma}(\omega)$:

$$\Delta\varepsilon_n \approx \varepsilon_n + \langle n | \hat{\Sigma}(\varepsilon_n + \Delta\varepsilon_n) - \hat{V}_{xc} | n \rangle$$

The expectation value of $\hat{\Sigma}(\omega)$ being :

$$\langle n | \hat{\Sigma}(\omega) | n \rangle = \frac{i}{2\pi} \sum_{n'} \int_{-\infty}^{+\infty} d\omega' \frac{\langle n | \langle n^* | \hat{\epsilon}^{\ominus}(\omega') \hat{v} | n^* \rangle | n \rangle}{\omega - (\varepsilon_{n'} - \varepsilon_n)}$$

where $\hat{v}$ is the coulomb operator and where :

$$\hat{\epsilon}(\omega) = \hat{1} - \hat{v}\hat{P}(\omega)$$

$$\hat{P}(\omega) = \sum_{c,v} |c^*\rangle |v\rangle \left[\frac{1}{\omega - (\varepsilon_c - \varepsilon_v)} - \frac{1}{\omega + (\varepsilon_c - \varepsilon_v)} \right] \langle v | \langle c^* |$$

○ : bottleneck #1 : sum over conduction states

○ : bottleneck #2 : inversion of the dielectric matrix

Solution to bottleneck 1

Sternheimer equation

Idea : transform $\sum$ into a linear equation problem...

$$\hat{P}(\omega)|\psi\rangle = \sum_{c,v} |c^*\rangle |v\rangle \left[\frac{1}{\omega - (\varepsilon_c - \varepsilon_v)} - \frac{1}{\omega + (\varepsilon_c - \varepsilon_v)} \right] \langle v | \langle c^* | |\psi\rangle$$

$$\equiv \sum_v |f_v^{+*}\rangle + |f_v^{-*}\rangle$$

$$\Rightarrow |f_v^{\pm}\rangle = -\sum_c \frac{|c\rangle \langle c|}{\varepsilon_c - \varepsilon_v \pm \omega} |\psi^*\rangle |v\rangle$$

$$= -\sum_c \frac{|c\rangle \langle c|}{\hat{H} - \varepsilon_v \pm \omega} |\psi^*\rangle |v\rangle$$

$$= -\frac{|c\rangle \langle c|}{\hat{H} - \varepsilon_v \pm \omega} |\psi^*\rangle |v\rangle$$

$$\Rightarrow (\hat{H} - \varepsilon_v \pm \omega) |f_v^{\pm}\rangle = -\hat{P}_c |\psi^*\rangle |v\rangle \quad (\text{Sternheimer's equation})$$

Implementation of solution

1) $H + FFTs = N \log N$ op. $\Rightarrow$ iterative method

2) $H - \varepsilon_v \pm \omega$ can be singular $\Rightarrow$ SQMR instead of CG

Solution to bottleneck 2

Lanczos algorithm

Usually, $\hat{\epsilon}(\omega)$ is expressed in a plane-wave basis.

Here, we decrease the size of the matrix by constructing a basis that automatically focuses on the relevant subspace :

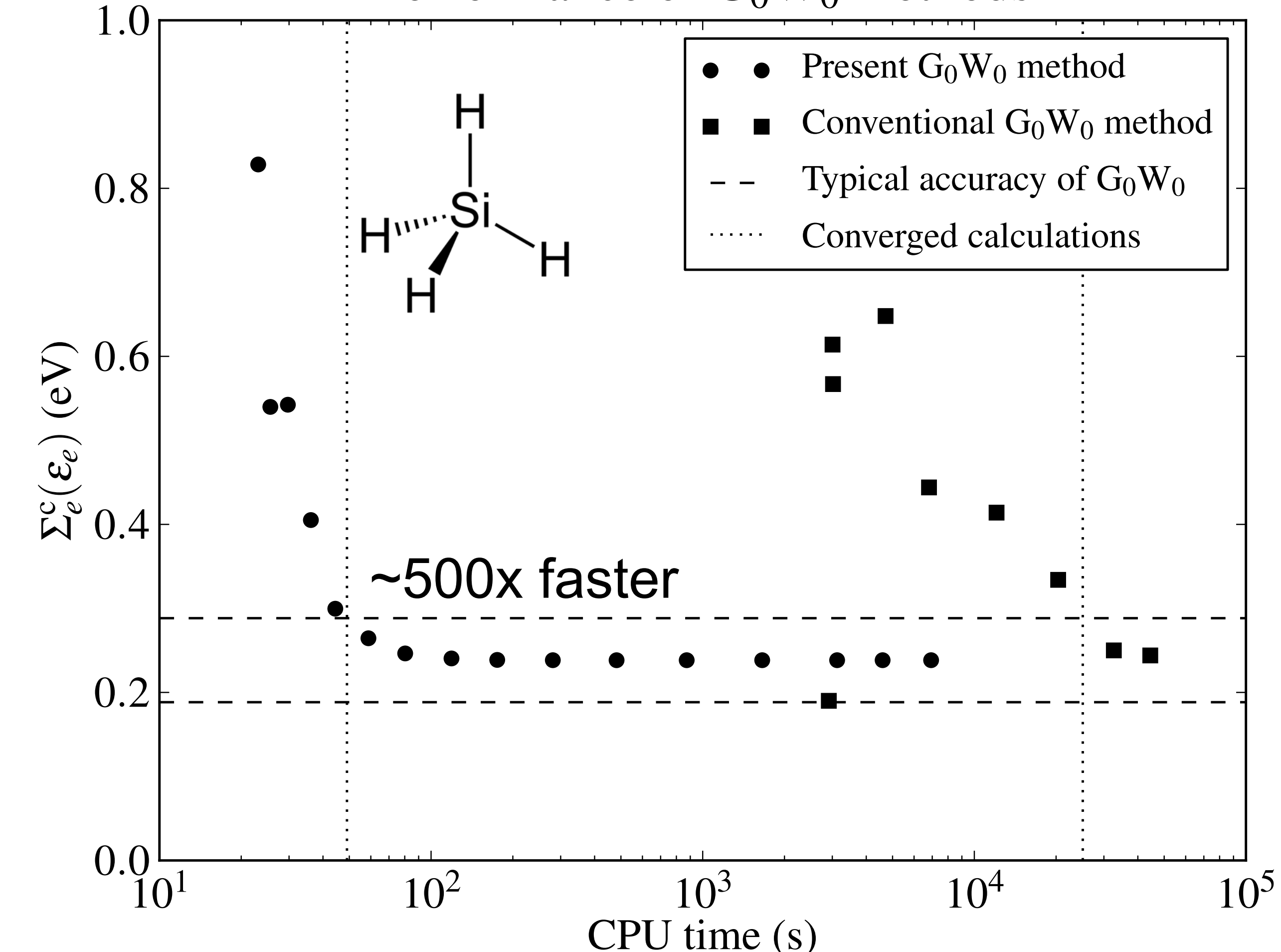
$$\{|\phi_0\rangle, \hat{\epsilon}(\omega)|\phi_0\rangle, \hat{\epsilon}^2(\omega)|\phi_0\rangle, \dots, \hat{\epsilon}^N(\omega)|\phi_0\rangle\}$$

and then orthonormalize it to obtain the Lanczos basis :

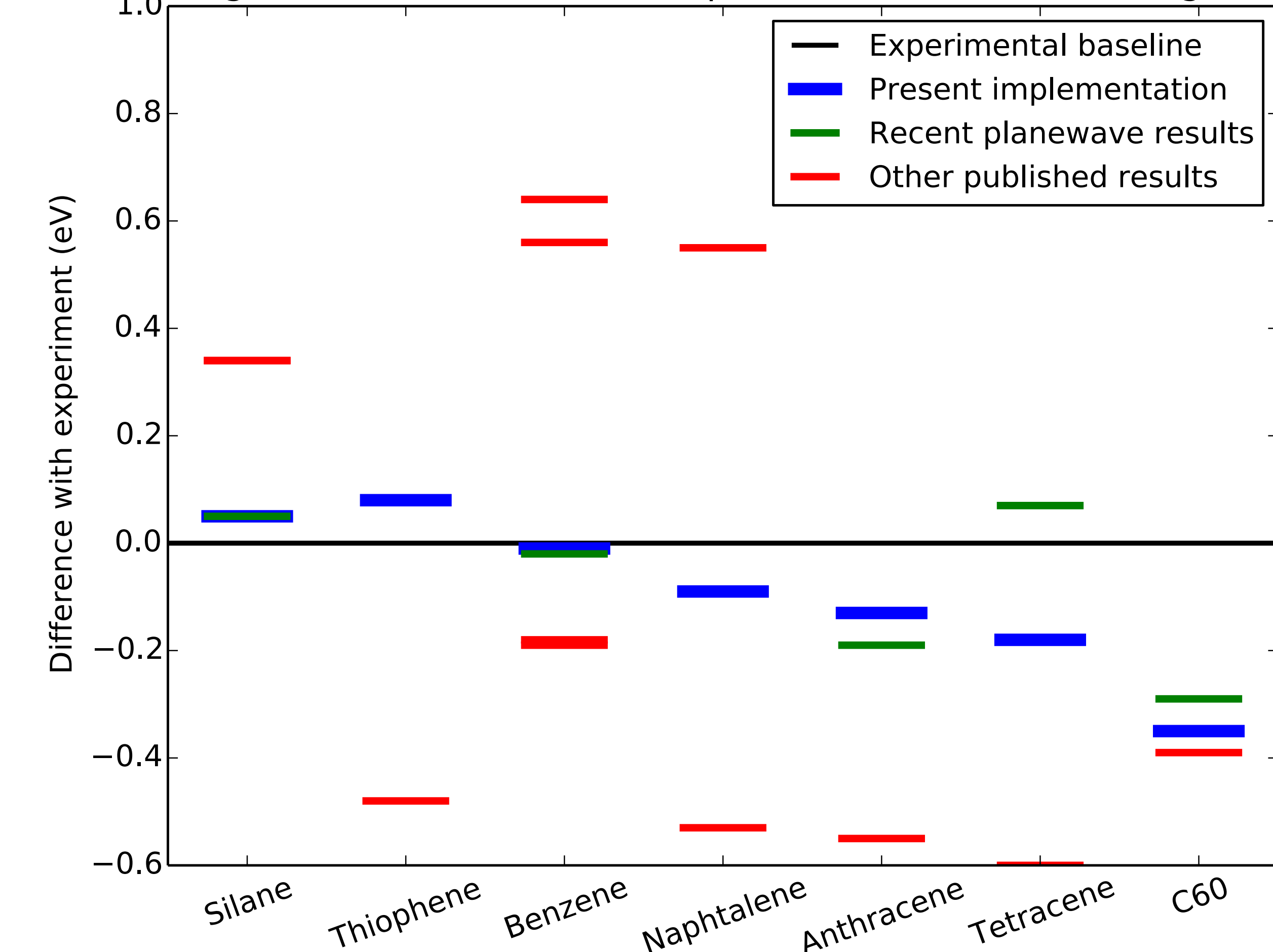
$$\{ |l_0(\omega)\rangle, |l_1(\omega)\rangle, |l_2(\omega)\rangle, \dots, |l_N(\omega)\rangle \}$$

which is substantially smaller than a plane-wave basis of equivalent accuracy.

Performance of G_0W_0 methods



Agreement of G_0W_0 with experimental ionization energies



Conclusion

- 2 bottlenecks in G_0W_0 implementations :
 1. The sum over conduction states
 2. The inversion of the dielectric matrix
- We assess these bottlenecks using :
 3. Sternheimer's equation
 4. Lanczos algorithm
- and obtain a 500-fold increase in speed
- without any further approximation

See [arXiv:1408.3036](https://arxiv.org/abs/1408.3036) for more details